

B1  
5. The nonvolatile semiconductor memory device according to claim [4] 16 wherein metal silicide films are formed on ~~the~~ surfaces of [a] said control gate, [a surface of a] said source diffusion layer and [a surface of a] said drain diffusion layer of each of said [transistor, respectively] transistors.

7. (Amended) The nonvolatile semiconductor memory device according to claim [1] 16 further comprising at least one of a low-voltage MOS transistor and a high-voltage MOS transistor as a peripheral circuit.

Sub D1  
B3  
Please add new claims 16-17 as follows:

--16. A nonvolatile semiconductor memory device comprising:

a semiconductor substrate;

memory transistors formed on said semiconductor substrate to perform nonvolatile storage of an electric charge in accordance with data, each of said memory transistors being an electrically rewritable memory transistor including a floating gate formed over said semiconductor substrate via a first gate insulating film and a control gate formed over said floating gate via a second gate insulating film;

an oxide film formed on said substrate and at least on both sides of each said floating gate and both sides of each said control gate;

side walls each for protecting sides of said floating gate and said control gate of each said transistor, each said side wall formed from a first silicon nitride film formed by low-pressure CVD over said oxide film;

a second silicon nitride film covering surfaces of said control gate, a source diffusion layer, a drain diffusion layer and each of said side walls of each of said memory transistors and on surfaces; and

a wiring layer formed over said second silicon nitride film via an inter-layer insulating film.

SUB C1  
17. The nonvolatile semiconductor memory device according to claim 16, wherein: memory regions extending in one direction and element separating regions extending in said one direction are alternately formed;